

LDO Regulator for RF and Analog Circuits - Ultra-Low Noise and High PSRR

250 mA

NCP160

The NCP160 is a linear regulator capable of supplying 250 mA output current. Designed to meet the requirements of RF and analog circuits, the NCP160 device provides low noise, high PSRR, low quiescent current, and very good load/line transients. The device is designed to work with a 1 µF input and a 1 µF output ceramic capacitor. It is available in two thickness ultra-small 0.35P, 0.64 mm x 0.64 mm Chip Scale Package (CSP) and XDFN-4 0.65P, 1 mm x 1 mm.

Features

- Operating Input Voltage Range: 1.9 V to 5.5 V
- Available in Fixed Voltage Option: 1.8 V to 5.14 V
- ±2% Accuracy Over Load/Temperature
- Ultra Low Quiescent Current Typ. 18 μA
- Standby Current: Typ. 0.1 μA
- Very Low Dropout: 80 mV at 250 mA
- Ultra High PSRR: Typ. 98 dB at 20 mA, f = 1 kHz
- Ultra Low Noise: 10 μV_{RMS}
- Stable with a 1 µF Small Case Size Ceramic Capacitors
- Available in -WLCSP4 0.64 mm x 0.64 mm x 0.4 mm
 - -WLCSP4 0.64 mm x 0.64 mm x 0.33 mm
 - -XDFN4 1 mm x 1 mm x 0.4 mm
- These Devices are Pb-Free and are RoHS Compliant

Typical Applications

- Battery-powered Equipment
- Wireless LAN Devices
- Smartphones, Tablets
- Cameras, DVRs, STB and Camcorders







WLCSP4 CASE 567JZ

WLCSP4 CASE 567KA

XDFN4 CASE 711AJ

MARKING DIAGRAMS

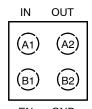






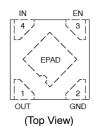
X or XX = Specific Device Code = Date Code

PIN CONNECTIONS



GND

(Top View)



ORDERING INFORMATION

See detailed ordering, marking and shipping information on page NO TAG of this data sheet.

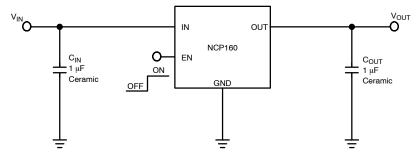


Figure 1. Typical Application Schematics

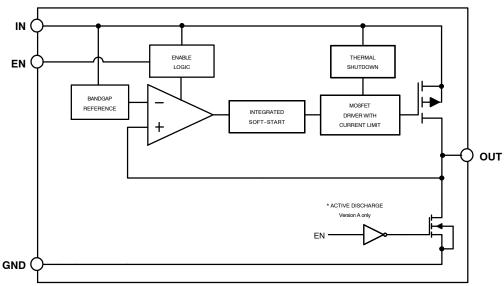


Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No. CSP4	Pin No. XDFN4	Pin Name	Description
A1	4	IN	Input voltage supply pin
A2	1	OUT	Regulated output voltage. The output should be bypassed with small 1 μ F ceramic capacitor.
B1	3	EN	Chip enable: Applying V_{EN} < 0.4 V disables the regulator, Pulling V_{EN} > 1.2 V enables the LDO.
B2	2	GND	Common ground connection
_	EPAD	EPAD	Expose pad can be tied to ground plane for better power dissipation

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	-0.3 V to 6	V
Output Voltage	V _{OUT}	-0.3 to V _{IN} + 0.3, max. 6	V
Chip Enable Input	V_{CE}	-0.3 V to 6	V
Output Short Circuit Duration	t _{SC}	unlimited	s
Maximum Junction Temperature	T_J	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and

- reliability may be affected.

 1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- This device series incorporates ESD protection and is tested by the following methods:
 ESD Human Body Model tested per EIA/JESD22–A114
 ESD Machine Model tested per EIA/JESD22–A115

Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

THERMAL CHARACTERISTICS

Rating		Value	Unit
Thermal Characteristics, CSP4 (Note 3) Thermal Resistance, Junction-to-Air	Б	108	2011
Thermal Characteristics, XDFN4 (Note 3) Thermal Resistance, Junction-to-Air	$R_{ hetaJA}$	198.1	°C/W

3. Measured according to JEDEC board specification. Detailed description of the board can be found in JESD51-7

 $\textbf{ELECTRICAL CHARACTERISTICS} - 40^{\circ}C \leq T_{J} \leq 125^{\circ}C; \ V_{IN} = V_{OUT(NOM)} + 1 \ V; \ I_{OUT} = 1 \ \text{mA}, \ C_{IN} = C_{OUT} = 1 \ \mu\text{F}, \ unless otherwise}$ noted. V_{EN} = 1.2 V. Typical values are at T_J = +25°C (Note 4).

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			V _{IN}	1.9		5.5	V
Output Voltage Accuracy	$V_{IN} = V_{OUT(NOM)} + 1 V$ 0 mA $\leq I_{OUT} \leq 250$ mA		V _{OUT}	-2		+2	%
Line Regulation	V _{OUT(NOM)} + 1 V ≤ V _{IN} ≤ 5.5 V		Line _{Reg}		0.02		%/V
Load Regulation	I _{OUT} = 1 m/	A to 250 mA	Load _{Reg}		0.001		%/mA
	V _{OUT(NOM)} = 1.8 V				180	250	
		V _{OUT(NOM)} = 2.5 V]		110	175	
		V _{OUT(NOM)} = 2.8 V			95	160	
		V _{OUT(NOM)} = 2.85 V			95	160	
		V _{OUT(NOM)} = 3.0 V			90	155	1
Dropout Voltage (Note 5)	I _{OUT} = 250 mA	V _{OUT(NOM)} = 3.2 V	V_{DO}		85	149	mV
		V _{OUT(NOM)} = 3.3 V			80	145	1
		V _{OUT(NOM)} = 3.5 V			75	140	1
		V _{OUT(NOM)} = 4.5 V			65	120	
		V _{OUT(NOM)} = 5.0 V			75	105	
		V _{OUT(NOM)} = 5.14 V			60	105	
Output Current Limit	V _{OUT} = 90% V _{OUT(NOM)}		I _{CL}	250	700		
Short Circuit Current	V _{OUT}	= 0 V	I _{SC}		690		mA
Quiescent Current	I _{OUT} =	- 0 mA	IQ		18	23	μΑ
Shutdown Current	V _{EN} ≤ 0.4 V	, V _{IN} = 4.8 V	I _{DIS}		0.01	1	μΑ
EN Pin Threshold Voltage	EN Input \	/oltage "H"	V _{ENH}	1.2			
	EN Input \	/oltage "L"	V _{ENL}			0.4	V
EN Pull Down Current	V _{EN} =	4.8 V	I _{EN}		0.2	0.5	μΑ
Turn-On Time	C _{OUT} = 1 μF, From V _{OUT} = 95%	assertion of V _{EN} to V _{OUT(NOM)}			120		μs
Power Supply Rejection Ratio	I _{OUT} = 20 mA	f = 100 Hz f = 1 kHz f = 10 kHz f = 100 kHz	PSRR		91 98 82 48		dB
Output Voltage Noise	f = 10 Hz to 100 kHz	I _{OUT} = 1 mA I _{OUT} = 250 mA	V _N		14 10		μV_{RMS}
Thermal Shutdown Threshold	Temperat	Temperature rising			160		°C
	Temperat	ure falling	T _{SDL}		140		°C
Active Output Discharge Resistance	V _{EN} < 0.4 V, Version A only		R _{DIS}		280		Ω
Line Transient (Note 6)	V _{IN} = (V _{OUT(NOM)} + 1.6 V) in 30 μs	1 V) to (V _{OUT(NOM)} + s, I _{OUT} = 1 mA	T	-1			>/
	V _{IN} = (V _{OUT(NOM)} + 1.6 V) to (V _{OUT(NOM)} + 1 V) in 30 μs, I _{OUT} = 1 mA		Tran _{LINE}			+1	mV
Load Transient (Note 6)	I _{OUT} = 1 mA to	200 mA in 10 μs	- Tran _{LOAD}	-40			mV
	I _{OUT} = 200 mA to 1mA in 10 μs		ITAIILOAD			+40	v

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T_A = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.

5. Dropout voltage is characterized when V_{OUT} falls 100 mV below V_{OUT(NOM)}.

6. Guaranteed by design.

TYPICAL CHARACTERISTICS

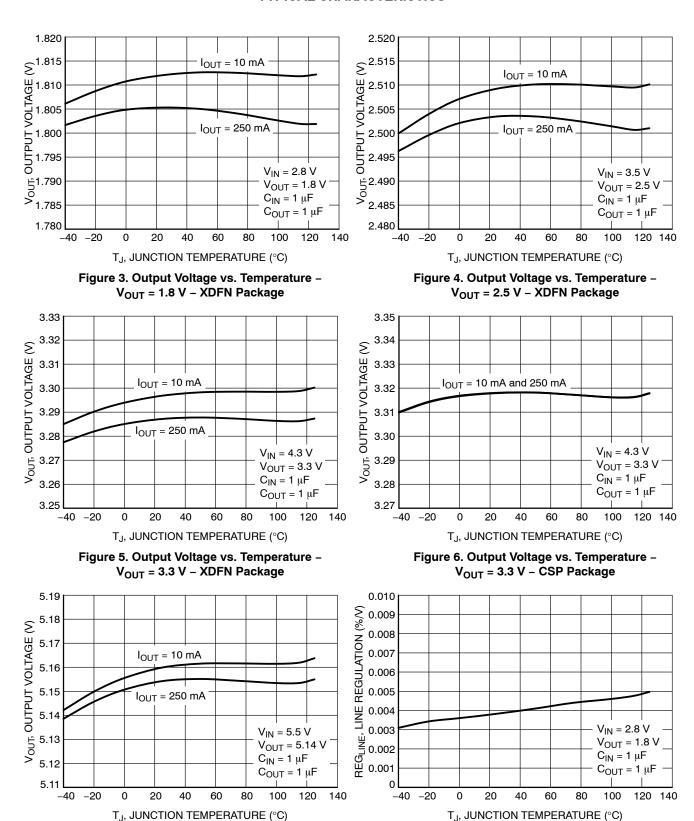


Figure 8. Line Regulation vs. Temperature -

V_{OUT} = 1.8 **V**

Figure 7. Output Voltage vs. Temperature -

V_{OUT} = 5.14 V - XDFN Package

TYPICAL CHARACTERISTICS

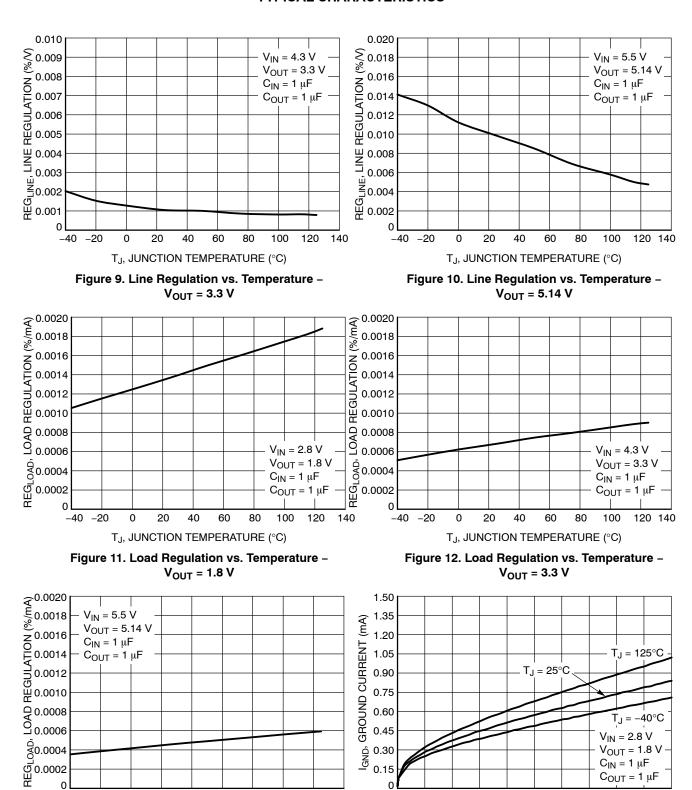


Figure 13. Load Regulation vs. Temperature – V_{OUT} = 5.14 V

T_J, JUNCTION TEMPERATURE (°C)

40

60

-40 -20

Figure 14. Ground Current vs. Load Current – $V_{OUT} = 1.8 \text{ V}$

I_{OUT}, OUTPUT CURRENT (mA)

125 150 175 200 225 250

25

0

50

120

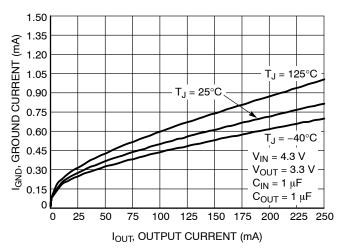


Figure 15. Ground Current vs. Load Current – $V_{OUT} = 3.3 \text{ V}$

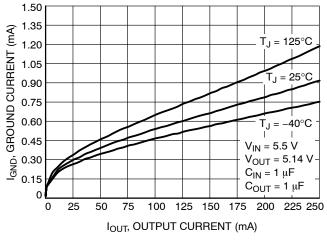


Figure 16. Ground Current vs. Load Current – V_{OUT} = 5.14 V

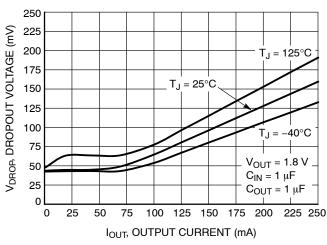


Figure 17. Dropout Voltage vs. Load Current – $V_{OUT} = 1.8 \text{ V}$

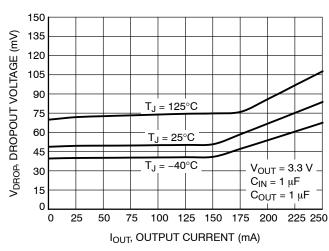


Figure 18. Dropout Voltage vs. Load Current – $V_{OUT} = 3.3 \text{ V}$

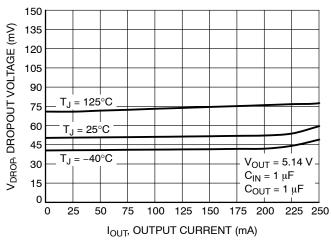


Figure 19. Dropout Voltage vs. Load Current – V_{OUT} = 5.14 V

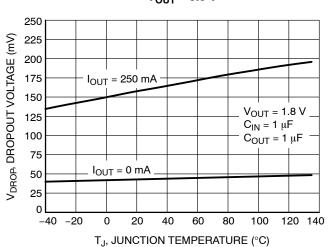
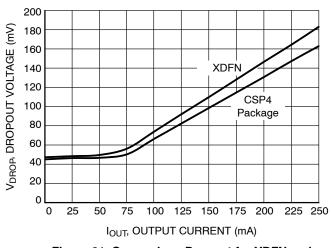


Figure 20. Dropout Voltage vs. Temperature– $V_{OUT} = 1.8 \text{ V}$



150 V_{DROP}, DROPOUT VOLTAGE (mV) 135 120 105 90 XDFN 75 60 CSP4 45 Package 30 15 0 25 75 100 125 150 175 200 225 250 0 50 I_{OUT}, OUTPUT CURRENT (mA)

Figure 21. Comparison Dropout for XDFN and CSP – 1.8 V

Figure 22. Comparison Dropout for XDFN and CSP – 3.3 V

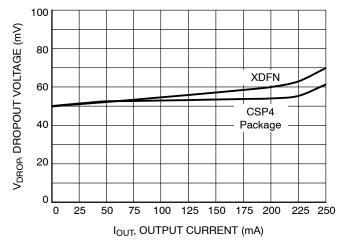
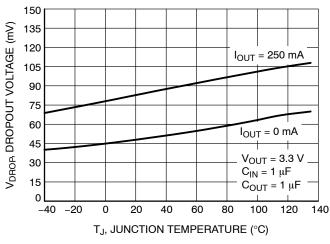


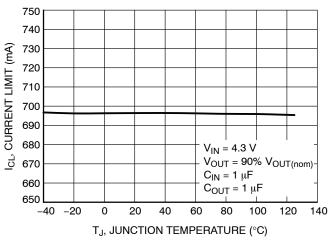
Figure 23. Comparison Dropout for XDFN and CSP – 5.14 V



100 V_{DROP}, DROPOUT VOLTAGE (mV) 90 I_{OUT} = 250 mA 80 70 60 I_{OUT} = 0 mA 50 40 30 $V_{OUT} = 5.14 V$ 20 $C_{IN} = 1 \, \mu F$ 10 $C_{OUT} = 1 \mu F$ 0 -20 20 40 60 80 100 120 140 -40 0 T_J, JUNCTION TEMPERATURE (°C)

Figure 24. Dropout Voltage vs. Temperature– $V_{OUT} = 3.3 \text{ V}$

Figure 25. Dropout Voltage vs. Temperature– $V_{OUT} = 5.14 \text{ V}$



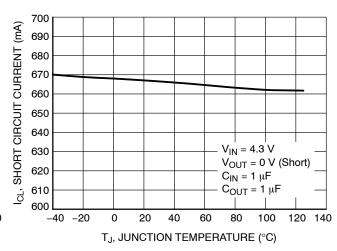
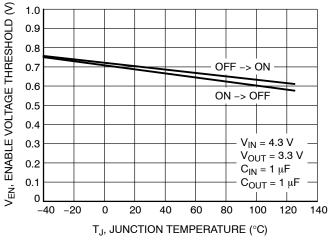


Figure 26. Current Limit vs. Temperature

Figure 27. Short Circuit Current vs. Temperature



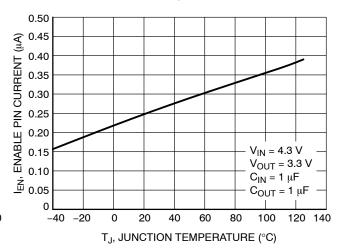
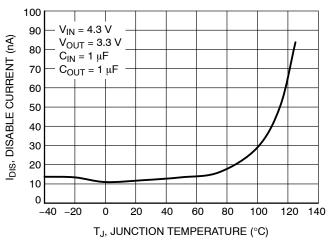


Figure 28. Enable Threshold Voltage vs. Temperature

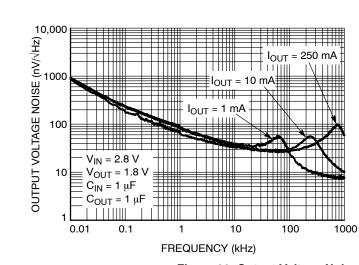
Figure 29. Enable Current Temperature



300 290 R_{DIS}, DISCHARGE RESISTIVITY 280 270 260 250 240 230 $V_{IN} = 4.3 V$ V_{OUT} = 3.3 V 220 $C_{IN} = 1 \mu F$ 210 $C_{OUT} = 1 \mu F$ 200 -40 -20 20 40 60 80 100 120 140 0 T_J, JUNCTION TEMPERATURE (°C)

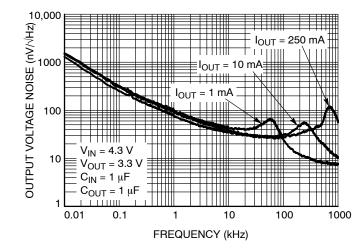
Figure 30. Disable Current vs. Temperature

Figure 31. Discharge Resistivity vs. Temperature



	RMS Output Noise (μV)			
Іоит	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	14.62	14.10		
10 mA	11.12	10.48		
250 mA	10.37	9.82		

Figure 32. Output Voltage Noise Spectral Density – V_{OUT} = 1.8 V



	RMS Output Noise (μV)				
lout	10 Hz – 100 kHz	100 Hz – 100 kHz			
1 mA	16.9	15.79			
10 mA	12.64	11.13			
250 mA	11.96	10.64			

Figure 33. Output Voltage Noise Spectral Density – V_{OUT} = 3.3 V

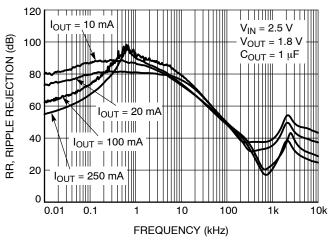


Figure 34. Power Supply Rejection Ratio, $V_{OUT} = 1.8 \text{ V}$

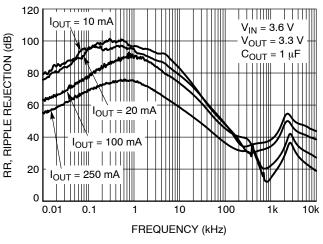


Figure 35. Power Supply Rejection Ratio, V_{OUT} = 3.3 V

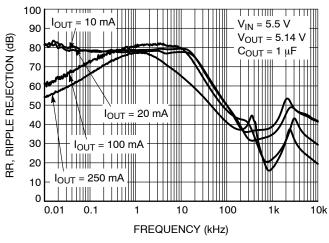


Figure 36. Power Supply Rejection Ratio, $V_{OUT} = 5.14 \text{ V}$

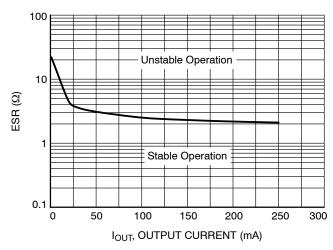


Figure 37. Stability vs. ESR

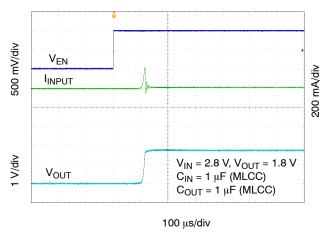


Figure 38. Enable Turn-on Response – C_{OUT} = 1 μ F, I_{OUT} = 10 mA

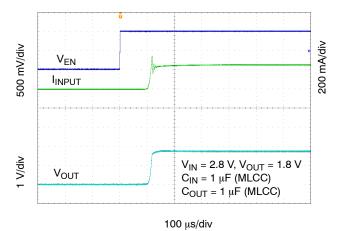


Figure 39. Enable Turn-on Response – $C_{OUT} = 1 \mu F$, $I_{OUT} = 250 \text{ mA}$

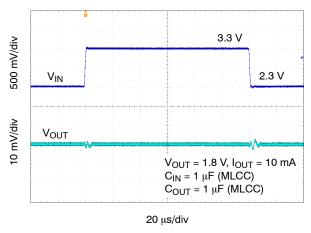


Figure 40. Line Transient Response – $V_{OUT} = 1.8 \text{ V}$

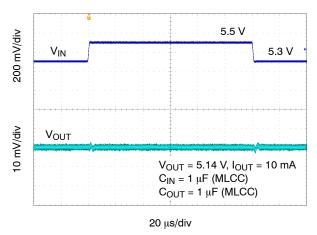


Figure 42. Line Transient Response – V_{OUT} = 5.14 V

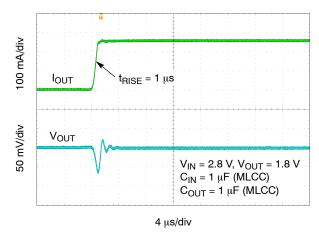


Figure 44. Load Transient Response – 1 mA to 250 mA – V_{OUT} = 1.8 V

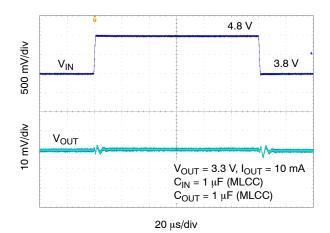


Figure 41. Line Transient Response – $V_{OUT} = 3.3 \text{ V}$

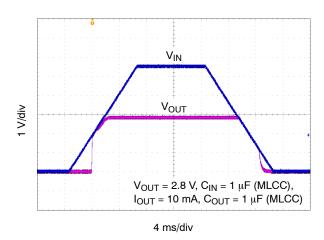


Figure 43. Turn-on/off - Slow Rising V_{IN}

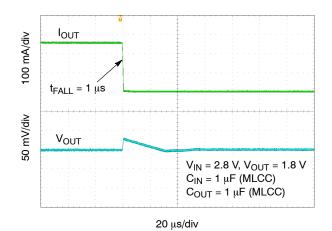


Figure 45. Load Transient Response – 250 mA to 1 mA – V_{OUT} = 1.8 V

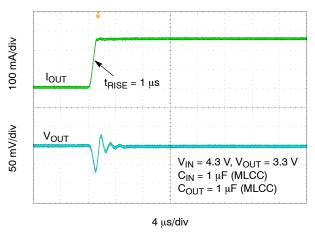


Figure 46. Load Transient Response – 1 mA to 250 mA – V_{OUT} = 3.3 V

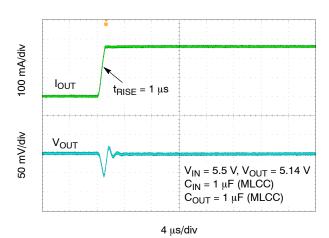


Figure 48. Load Transient Response – 1 mA to 250 mA – V_{OUT} = 5.14 V

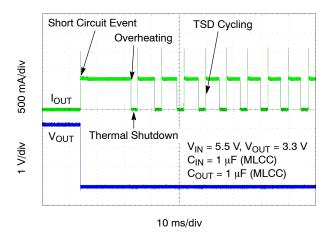


Figure 50. Short Circuit and Thermal Shutdown

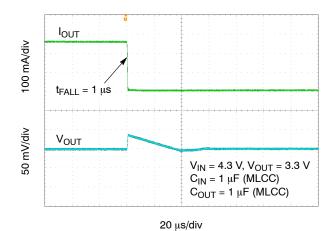


Figure 47. Load Transient Response – 250 mA to 1 mA – V_{OUT} = 3.3 V

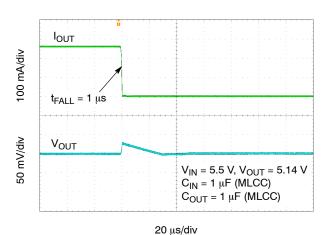


Figure 49. Load Transient Response – 250 mA to 1 mA – V_{OUT} = 5.14 V

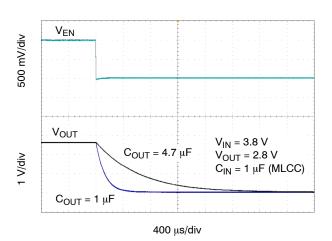


Figure 51. Enable Turn-off

APPLICATIONS INFORMATION

General

The NCP160 is an ultra-low noise 250 mA low dropout regulator designed to meet the requirements of RF applications and high performance analog circuits. The NCP160 device provides very high PSRR and excellent dynamic response. In connection with low quiescent current this device is well suitable for battery powered application such as cell phones, tablets and other. The NCP160 is fully protected in case of current overload, output short circuit and overheating.

Input Capacitor Selection (CIN)

Input capacitor connected as close as possible is necessary for ensure device stability. The X7R or X5R capacitor should be used for reliable performance over temperature range. The value of the input capacitor should be 1 μF or greater to ensure the best dynamic performance. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes.

Output Decoupling (COUT)

The NCP160 requires an output capacitor connected as close as possible to the output pin of the regulator. The recommended capacitor value is 1 μF and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The NCP160 is designed to remain stable with minimum effective capacitance of 0.7 μF to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0201 the effective capacitance drops rapidly with the applied DC bias. Please refer Figure 52.

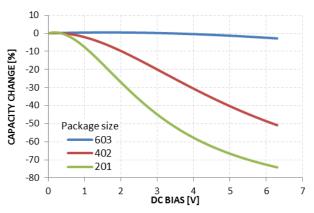


Figure 52. Capacity vs DC Bias Voltage

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the C_{OUT} but the maximum value of ESR should be less than $2\,\Omega$. Larger output capacitors and lower ESR could improve the load

transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

Enable Operation

The NCP160 uses the EN pin to enable/disable its device and to deactivate/activate the active discharge function.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned—off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage V_{OUT} is pulled to GND through a 280 Ω resistor. In the disable state the device consumes as low as typ. 10 nA from the V_{IN} .

If the EN pin voltage >1.2 V the device is guaranteed to be enabled. The NCP160 regulates the output voltage and the active discharge transistor is turned–off.

The EN pin has internal pull-down current source with typ. value of 200 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

Output Current Limit

Output Current is internally limited within the IC to a typical 700 mA. The NCP60 will source this amount of current measured with a voltage drops on the 90% of the nominal V_{OUT} . If the Output Voltage is directly shorted to ground ($V_{OUT} = 0$ V), the short circuit protection will limit the output current to 690 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration.

Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ($T_{SD}-160^{\circ}\text{C}$ typical), Thermal Shutdown event is detected and the device is disabled. The IC will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ($T_{SDU}-140^{\circ}\text{C}$ typical). Once the IC temperature falls below the 140°C the LDO is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking.

Power Dissipation

As power dissipated in the NCP160 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the NCP160 can handle is given by:

$$P_{D(MAX)} = \frac{\left[125^{\circ}C - T_{A}\right]}{\theta_{1A}}$$
 (eq. 1)

The power dissipated by the NCP160 for given application conditions can be calculated from the following equations:

$$P_D \approx V_{IN} \cdot I_{GND} + I_{OUT} (V_{IN} - V_{OUT})$$
 (eq. 2)

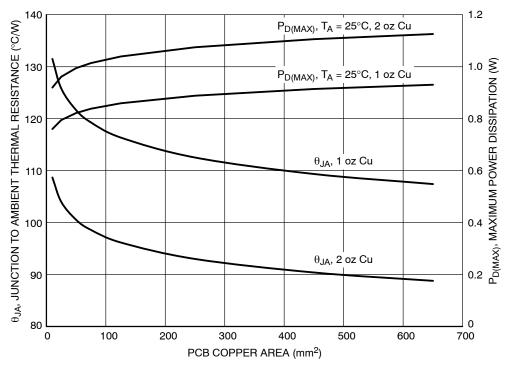


Figure 53. θ_{JA} and $P_{D\;(MAX)}$ vs. Copper Area (CSP4)

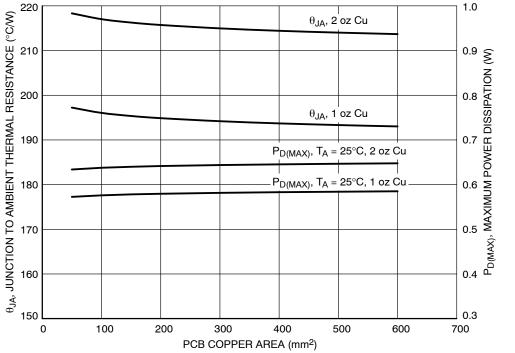


Figure 54. θ_{JA} and $P_{D\;(MAX)}$ vs. Copper Area (XDFN4)

Reverse Current

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that $V_{OUT} > V_{IN}$. Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

Power Supply Rejection Ratio

The NCP160 features very high Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range $100~\rm kHz-10~MHz$ can be tuned by the selection of C_{OUT} capacitor and proper PCB layout.

Turn-On Time

The turn-on time is defined as the time period from EN assertion to the point in which V_{OUT} will reach 98% of its nominal value. This time is dependent on various application conditions such as $V_{OUT(NOM)}$, C_{OUT} , T_A .

PCB Layout Recommendations

To obtain good transient performance and good regulation characteristics place $C_{\rm IN}$ and $C_{\rm OUT}$ capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 or 0201 capacitors with appropriate capacity. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad can be tied to the GND pin for improvement power dissipation and lower device temperature.

ORDERING INFORMATION

Device	Nominal Output Voltage	Description	Marking	Rotation	Package	Shipping [†]
NCP160AFCS180T2G	1.8 V		Α	0°		
NCP160AFCS250T2G	2.5 V	050 4 4 11 51 1	D	0°		
NCP160AFCS270T2G	2.7 V	250 mA, Active Discharge	4	0°		
NCP160AFCS280T2G	2.8 V		Е	0°		
NCP160AFCSC280T2G	2.8 V	250 mA, Active Discharge, Backside Coating	E	0°		
NCP160AFCS285T2G	2.85 V		F	0°		
NCP160AFCS2925T2G	2.925 V		Т	0°		
NCP160AFCS300T2G	3.0 V		J	0°		5000 /
NCP160AFCS320T2G	3.2 V	250 mA, Active Discharge	V	0°		
NCP160AFCS330T2G	3.3 V		K	0°	WLCSP4	
NCP160AFCS350T2G	3.5 V		L	0°		
NCP160AFCS370T2G	3.7 V		Y	0°		
NCP160AFCS450T2G	4.5 V		Р	0°	CASE 567KA	Tape &
NCP160AFCS500T2G	5.0 V		R	0°	(Pb-Free)	Reel
NCP160AFCS514T2G	5.14 V		Q	0°		
NCP160BFCS180T2G	1.8 V		Α	90°		
NCP160BFCS250T2G	2.5 V		D	90°		
NCP160BFCS280T2G	2.8 V		E	90°		
NCP160BFCS285T2G	2.85 V		F	90°		
NCP160BFCS2925T2G	2.925 V		Т	90°		
NCP160BFCS300T2G	3.0 V	250 mA, Non-Active Discharge	J	90°		
NCP160BFCS330T2G	3.3 V	Districtings	K	90°		
NCP160BFCS350T2G	3.5 V		L	90°		
NCP160BFCS450T2G	4.5 V		Р	90°		
NCP160BFCS500T2G	5.0 V		R	90°		
NCP160BFCS514T2G	5.14 V		Q	90°		

ORDERING INFORMATION (continued)

Device	Nominal Output Voltage	Description	Marking	Rotation	Package	Shipping [†]
NCP160AFCT180T2G	1.8 V		А	0°		
NCP160AFCT250T2G	2.5 V		D	0°	1	
NCP160AFCT270T2G	2.7 V		Т	0°	1	
NCP160AFCT280T2G	2.8 V	250 mA, Active Discharge	E	0°	1	
NCP160AFCT285T2G	2.85 V		F	0°	1	
NCP160AFCT300T2G	3.0 V		J	0°	1	
NCP160AFCT330T2G	3.3 V		K	0°	1	
NCP160AFCTC330T2G	3.3 V	250 mA, Active Discharge, Backside Coating	К	0°		
NCP160AFCT350T2G	3.5 V		L	0°	1	
NCP160AFCT450T2G	4.5 V	OSO w A Asti a Disabawa	Р	0°	WLCSP4 CASE 567JZ (Pb-Free)	
NCP160AFCT500T2G	5.0 V	250 mA, Active Discharge	R	0°		5000 / Tape & Reel
NCP160AFCT514T2G	5.14 V		Q	0°		
NCP160AFCTC180T2G	1.8 V	250 mA, Active Discharge, Backside Coating	Α	0°		
NCP160BFCT180T2G	1.8 V		Α	90°	1	
NCP160BFCT210T2G	2.1 V		Т	90°	1	
NCP160BFCT250T2G	2.5 V		D	90°	1	
NCP160BFCT280T2G	2.8 V		E	90°	1	
NCP160BFCT285T2G	2.85 V		F	90°	1	
NCP160BFCT300T2G	3.0 V	250 mA, Non-Active Discharge	J	90°	1	
NCP160BFCT330T2G	3.3 V	Diodiaigo	K	90°	1	
NCP160BFCT350T2G	3.5 V		L	90°	1	
NCP160BFCT450T2G	4.5 V		Р	90°	1	
NCP160BFCT500T2G	5.0 V		R	90°	1	
NCP160BFCT514T2G	5.14 V	1	Q	90°	1	

ORDERING INFORMATION (continued)

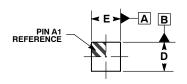
Device	Nominal Output Voltage	Description	Marking	Package	Shipping [†]
NCP160AMX180TBG	1.8 V		DF		
NCP160AMX1825TBG	1.825 V		D7	1	
NCP160AMX250TBG	2.5 V		DG		
NCP160AMX270TBG	2.7 V		D6		
NCP160AMX275TBG	2.75 V		D2		
NCP160AMX280TBG	2.8 V	250 mA, Active Discharge	DH		
NCP160AMX285TBG	2.85 V		DJ		
NCP160AMX290TBG	2.9 V		D4		
NCP160AMX300TBG	3.0 V		DK		
NCP160AMX320TBG	3.2 V		DY		3000 / Tape & Reel
NCP160AMX310TBG	3.1 V		D3	XDFN4 (Pb-Free)	
NCP160AMX330TBG	3.3 V		DA		
NCP160AMX350TBG	3.5 V		DL		
NCP160AMX450TBG	4.5 V		DM		
NCP160AMX500TBG	5.0 V		DW		
NCP160AMX514TBG	5.14 V		DC		
NCP160BMX180TBG	1.8 V		EF		
NCP160BMX1825TBG	1.825 V		E7		
NCP160BMX250TBG	2.5 V		EG		
NCP160BMX275TBG	2.75 V		E2		
NCP160BMX280TBG	2.8 V		EH		
NCP160BMX285TBG	2.85 V	OFO and Non Action Discharge	EJ		
NCP160BMX300TBG	3.0 V	250 mA, Non-Active Discharge	EK		
NCP160BMX330TBG	3.3 V		EA		
NCP160BMX350TBG	3.5 V		EL		
NCP160BMX450TBG	4.5 V		EM	1	
NCP160BMX500TBG	5.0 V		EW	1	
NCP160BMX514TBG	5.14 V		EC	1	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

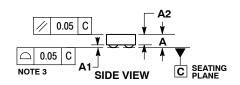


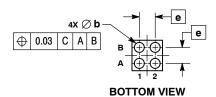
WLCSP4, 0.64x0.64 CASE 567JZ **ISSUE A**

DATE 03 AUG 2016



TOP VIEW



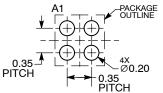


NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α			0.33		
A1	0.04	0.06	0.08		
A2		0.23 REF			
b	0.195	0.210	0.225		
D	0.610	0.640	0.670		
E	0.610	0.640	0.670		
е		0.35 BSC			

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	WLCSP4, 0.64X0.64		PAGE 1 OF 1	

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MECHANICAL CASE OUTLINE

SCALE 4:1

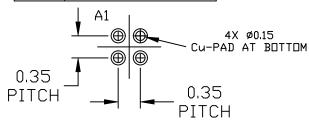
WLCSP4, 0.64x0.64 CASE 567KA ISSUE B

DATE 24 MAR 2020

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DATUM C, THE SEATING PLANE, IS DEFINED BY THE SPERICAL CROWNS OF THE CONTACT BALLS.
- 4. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE CONTACT BALLS.
- 5. DIMENSION 6 IS MEASURED AT THE MAXIMUM CONTACT BALL DIAMETER PARALLEL TO DATUM C.

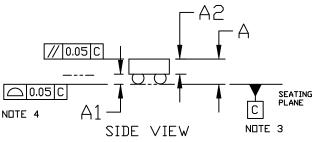
	MI	MILLIMETERS				
DIM	MIN.	N□M.	MAX.			
Α	0.355	0.405	0.455			
A1	0.13	0.15	0.17			
A2		0.255 RI	EF			
b	0.167	0.187	0.207			
D	0.610	0.640	0.670			
E	0.610	0.640	0.670			
е		0.35 BSC				

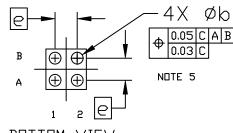


RECOMMENDED MOUNTING FOOTPRINT* (NSMD PAD TYPE)

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

PIN A1 REFERENCE TOP VIEW





BOTTOM VIEW

GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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PIN ONE

REFERENCE

2X 0.05 C

2X 0.05 C

// 0.05 C

□ 0.05 C

NOTE 4

XDFN4 1.0x1.0, 0.65P CASE 711AJ ISSUE C

В

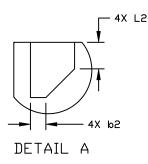
(A3)

SEATING

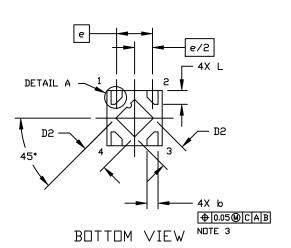
DATE 08 MAR 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION & APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.20 FROM THE TERMINAL TIPS.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

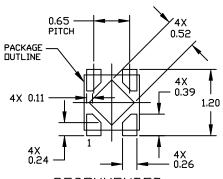


	MILLIMETERS			
DIM	MIN	NDM	MAX	
Α	0.33	0.38	0.43	
A1	0.00	-	0.05	
A3	0.10 REF			
b	0.15	0.20	0.25	
b2	0.02	0.07	0.12	
D	0.90	1.00	1.10	
D2	0.43	0.48	0.53	
Ε	0.90	1.00	1.10	
е	0.65 BSC			
L	0.20		0.30	
L2	0.07		0.17	



TOP VIEW

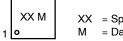
SIDE VIEW



RECOMMENDED MOUNTING FOOTPRINT

* FOR ADDITIONAL INFORMATION ON OUR PO-FRE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNT TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	XDFN4, 1.0X1.0, 0.65P		PAGE 1 OF 1	

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